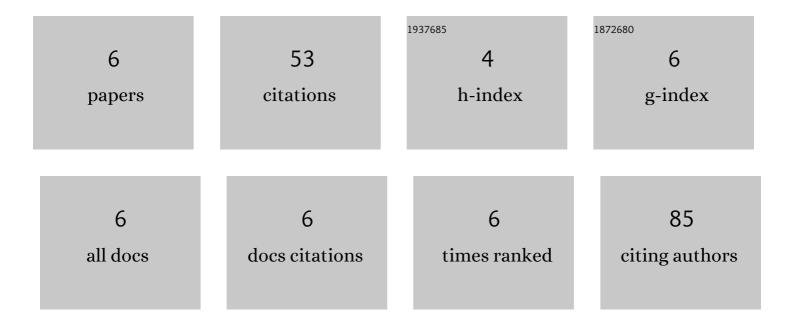
## Xin-Yuan Zhao

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Effects of HfO <sub>2</sub> encapsulation on electrical performances of few-layered MoS <sub>2</sub> transistor with ALD HfO <sub>2</sub> as back-gate dielectric. Nanotechnology, 2018, 29, 345201.	2.6	30
2	Improved Electrical Properties of Top-Gate MoS <sub>2</sub> Transistor With NH <sub>3</sub> -Plasma Treated HfO <sub>2</sub> as Gate Dielectric. IEEE Electron Device Letters, 2020, 41, 1364-1367.	3.9	6
3	Influence of Si-Substrate Concentration on Electrical Properties of Back- and Top-Gate MoSâ,, Transistors. IEEE Transactions on Electron Devices, 2021, 68, 3087-3090.	3.0	5
4	Repair of Oxygen Vacancies and Improvement of HfO <sub>2</sub> /MoS <sub>2</sub> Interface by NH <sub>3</sub> -Plasma Treatment. IEEE Transactions on Electron Devices, 2019, 66, 4337-4342.	3.0	4
5	Improved electrical performance of multilayer MoS <sub>2</sub> transistor by incorporating Al into host HfO <sub>2</sub> 2 as gate dielectric. Applied Physics Express, 2019, 12, 064005.	2.4	4
6	Improved Interfacial and Electrical Properties of MoS2 Transistor With High/Low-Temperature Grown Hf0.5Al0.5O as Top-Gate Dielectric. IEEE Electron Device Letters, 2020, 41, 385-388.	3.9	4